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North-Holland, Amsterdam

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– aluminum garnet, scandium substituted **84** (1987) 399
– barium copper oxide **84** (1987) 332; **87** (1988) 157; **85** (1987) 569, 581, 585, 588, 593, 607, 615, 623, 639, 652, 656; **87** (1988) 157; **88** (1988) 541; **89** (1988) 93
– barium copper oxide, sulphur substituted **85** (1987) 628
– iron garnet **82** (1987) 501, 652; **83** (1987) 15; **87** (1988) 331; **89** (1988) 267
– iron garnet, bismuth and gallium substituted **84** (1987) 323
– iron garnet, manganese doped **83** (1987) 543
– iron garnet, scandium substituted **85** (1987) 270

Zinc **82** (1987) 459; **84** (1987) 185; **85** (1987) 472; **87** (1988) 1
– chalcogenides **84** (1987) 425; **88** (1988) 193
– chromate **89** (1988) 267
– organic **82** (1987) 628; **86** (1988) 210, 248, 252, 257, 263, 268, 273, 279, 285, 290, 367; **87** (1988) 205; **89** (1988) 365
– oxide **86** (1988) 248, 410, 528, 906; **89** (1988) 365
– phosphide **86** (1988) 423, 430; **87** (1988) 567
– selenide **81** (1987) 43, 491, 495, 512, 518; **84** (1987) 1, 11, 199, 552; **86** (1988) 28, 132, 263, 268, 273, 279, 285, 318, 324, 329, 335, 342, 467, 609, 859, 873, 929, 935; **87** (1988) 581; **88** (1988) 415
– selenide sulphate **89** (1988) 331, 378
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– sulpho-selenide **86** (1988) 311
– telluride **81** (1987) 43, 495; **86** (1988) 1, 33, 210, 296, 436; **88** (1988) 522
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Zirconium
– carbide **87** (1988) 101
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